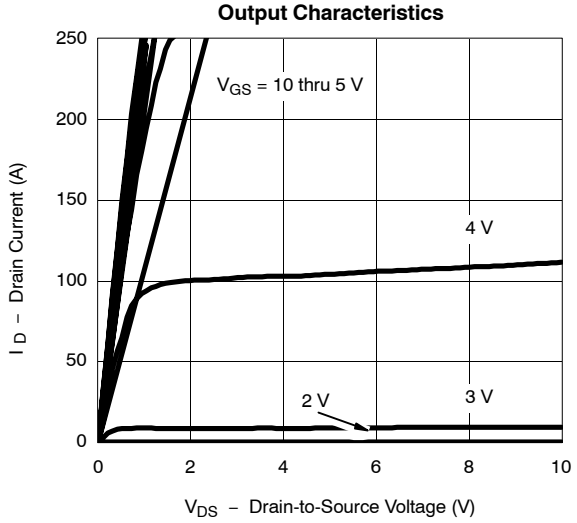
SPECIFICATIONS (T_J =25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{DS} = 0 V, I_D = 250 µA	30			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1		3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 125°C			50	
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 175°C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	120			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.0033	0.0042	Ω
		V_{GS} = 10 V, I_D = 20 A, T_J = 125°C			0.0063	
		V_{GS} = 10 V, I_D = 20 A, T_J = 175°C			0.0076	
		V_{GS} = 4.5 V, I_D = 20 A		0.0052	0.0065	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 20 A	20			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		5100		pF
Output Capacitance	C_{oss}			860		
Reverse Transfer Capacitance	C_{rss}			430		
Gate-Resistance	R_g		0.5	1.0	1.7	Ω
Total Gate Charge[b]	Q_g	V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 50 A		40	60	nC
Gate-Source Charge[b]	Q_{gs}			18		
Gate-Drain Charge[b]	Q_{gd}			16		
Turn-On Delay Time[b]	$t_{d(on)}$	V_{DD} = 15 V, R_L = 0.3 Ω I_D ≅ 50 A, V_{GEN} = 10 V, R_g = 2.5 Ω		12	20	ns
Rise Time[b]	t_r			12	20	
Turn-Off Delay Time[b]	$t_{d(off)}$			40	60	
Fall Time[b]	t_f			10	15	
Source-Drain Diode Ratings and Characteristics (T_C = 25°C)[c]						
Continuous Current	I_S				100	A
Pulsed Current	I_{SM}				300	
Forward Voltage[a]	V_{SD}	I_F = 30 A, V_{GS} = 0 V		1.2	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 50 A, di/dt = 100 A/µs		40	80	ns

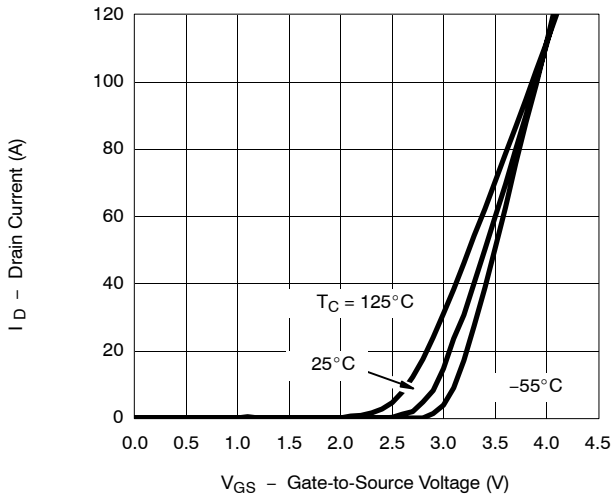
Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
b. Independent of operating temperature.
c. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

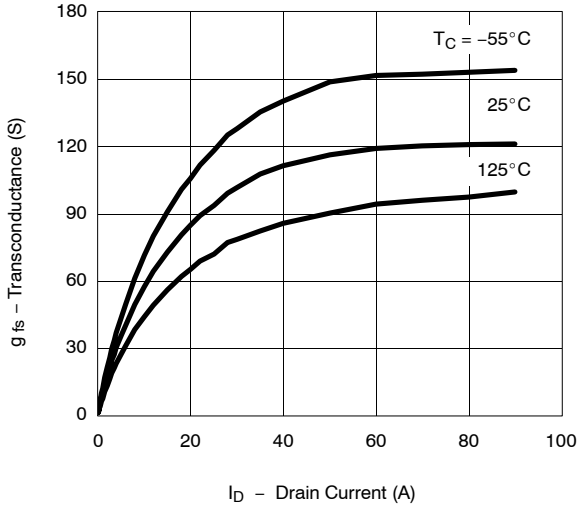
Output Characteristics



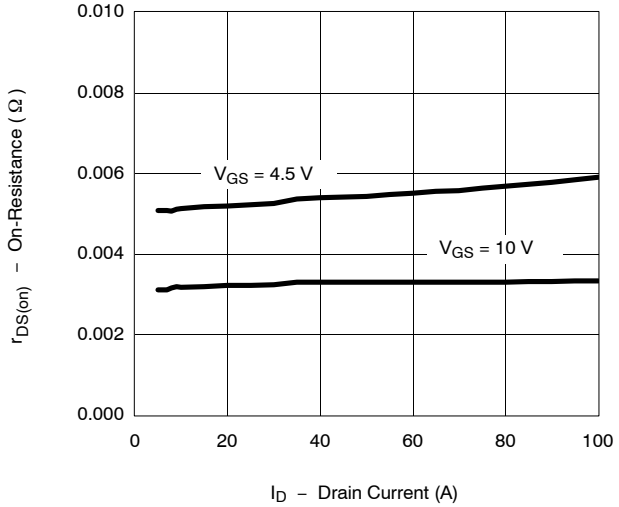
Transfer Characteristics



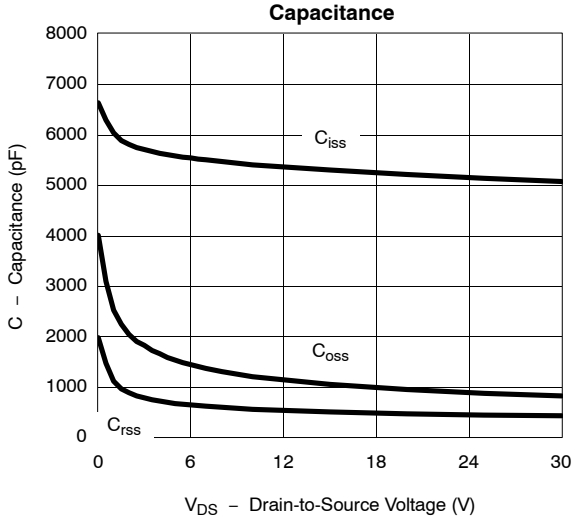
Transconductance



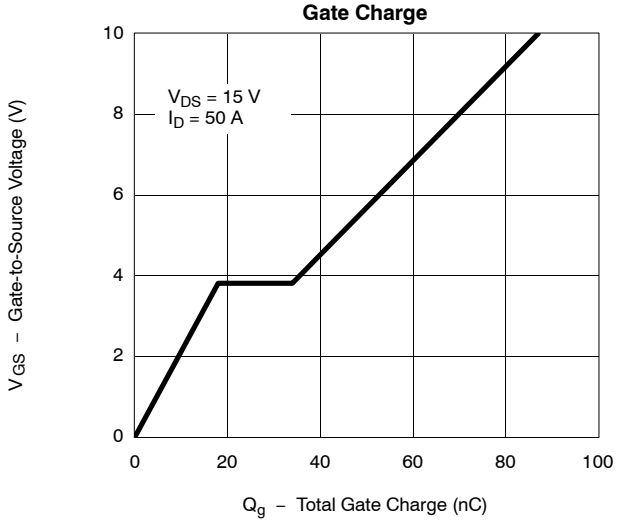
On-Resistance vs. Drain Current



Capacitance

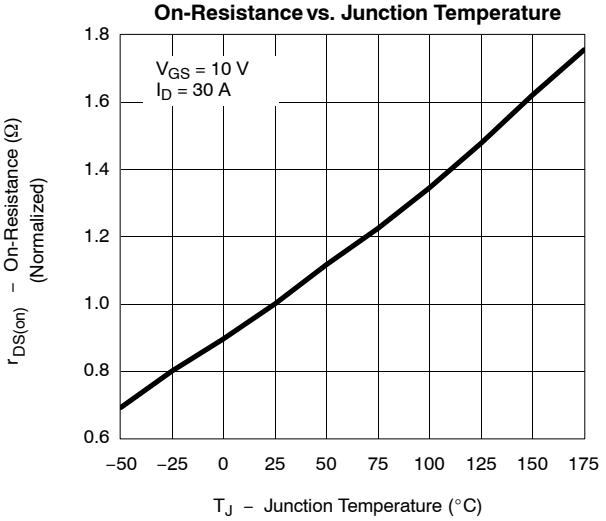


Gate Charge

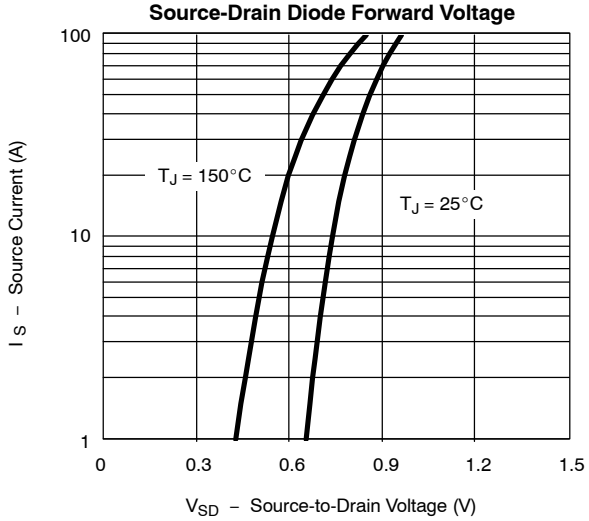


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

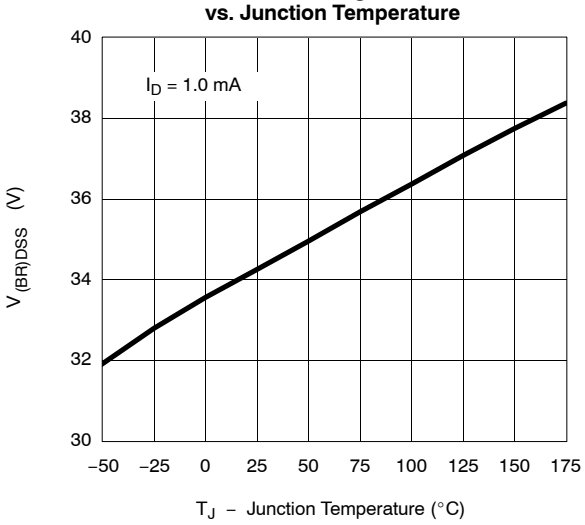
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

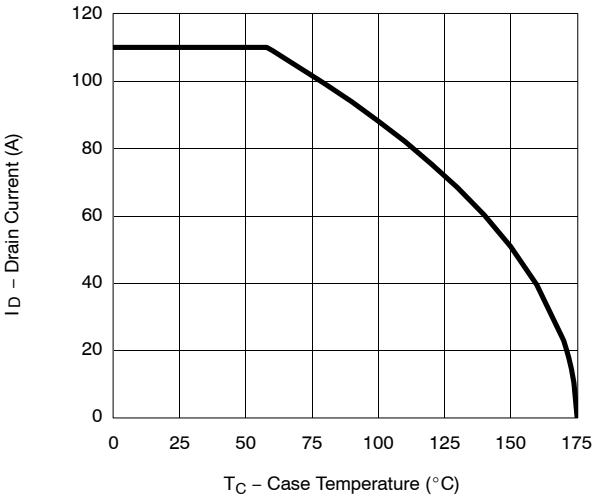


Drain-Source Voltage Breakdown vs. Junction Temperature

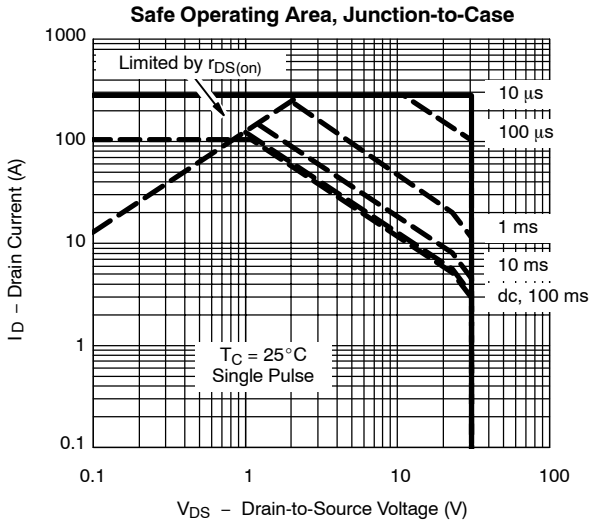


THERMAL RATINGS

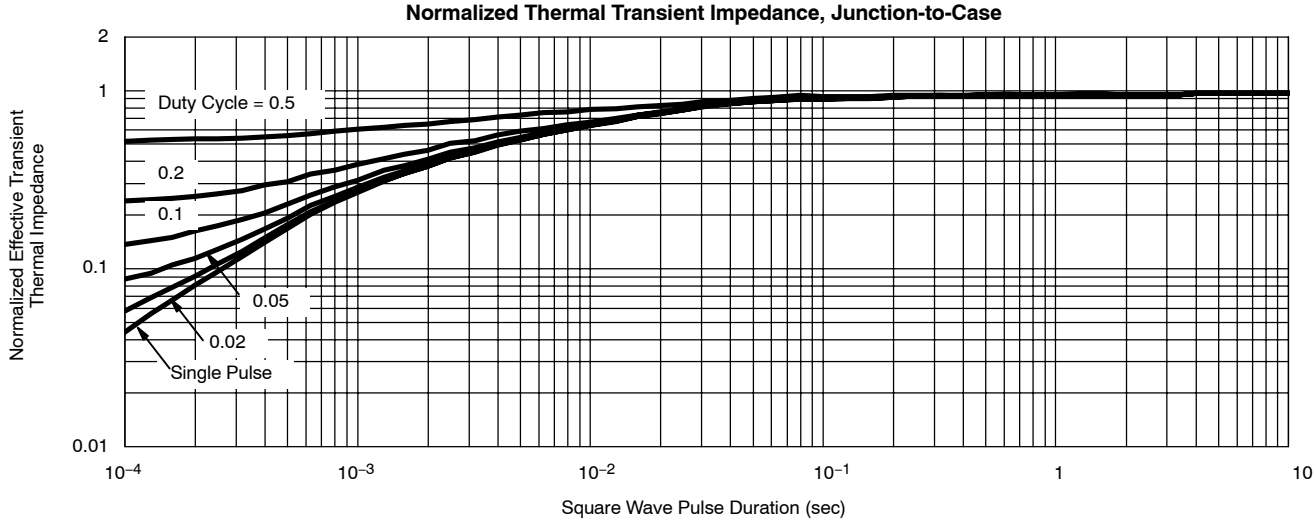
Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Case



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